

MOS INTEGRATED CIRCUIT μ PD78P368A

16/8 BIT SINGLE-CHIP MICROCOMPUTER

The μPD78P368A is produced by replacing the internal mask ROM of the μPD78366A with a one-time PROM or EPROM. One-time PROM products, in which data can be written once are effective for manufacture of small quantities of multiple products and early stage start-up of application. EPROM products, to which programs can be re-written after previously written programs have been erased, are suited for system evaluation.

The following user's manual describes the details of functions. Be sure to read it before design.

 μ PD78366A User's Manual, Hardware: U10205E μ PD78356 User's Manual, Instructions: IEU-1395

FEATURES

- Compatible with the μPD78366A
 - Can be replaced with the μ PD78366A containing mask ROM on a full-production basis.
- Internal PROM: 48K bytes
 - Data can be written once (one-time PROM product without an erasure window)
 - · Written data can be erased by exposure to ultraviolet light and re-written electrically (EPROM product with an
- PROM programming characteristics: Compatible with the μ PD27C1001A
- QTOPTM microcomputer

Remark The QTOP microcomputer is a single-chip microcomputer with a built-in one-time PROM that is totally supported by NEC. The support includes writing application programs, marking, screening, and verification.

ORDERING INFORMATION

Part number	Package	Internal ROM
μPD78P368AGF-3B9 μPD78P368AKL-S Note	80-pin plastic QFP (14 \times 20 mm) 80-pin ceramic WQFN	One-time PROM EPROM

Note Under development

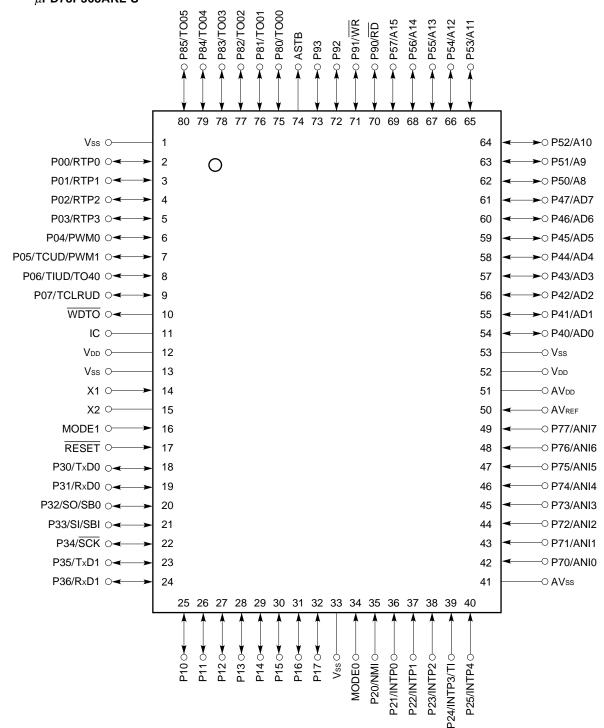
In this manual, the description of the PROM is for both a one-time PROM and EPROM.

The information in this document is subject to change without notice.



PIN CONFIGURATION (TOP VIEW)

- (1) Normal operation mode (MODE0 = L, MODE1 = L)
 - 80-pin plastic QFP (14 \times 20 mm) μ PD78P368AGF-3B9
 - 80-pin ceramic WQFN μPD78P368AKL-S



Caution Directly connect the IC pin to Vss.

Remark Pin compatible with the μ PD78366AGF



P00-P07: Port 0 P10-P17: Port 1 P20-P25: Port 2 P30-P36: Port 3 Port 4 P40-P47: P50-P57: Port 5 P70-P77: Port 7 P80-P85: Port 8 P90-P93: Port 9

RTP0-RTP3: Real-time port

Nonmaskable interrupt NMI: INTP0-INTP4: Interrupt from peripherals

TO00-TO05, TO40: Timer output TI: Timer input

TIUD: Timer input for up/down

counter

TCUD: Timer control for up/down

counter

TCLRUD: Timer clear for up/down

counter

ANIO-ANI7: Analog input TxD0, TxD1: Transmit data RxD0, RxD1: Receive data

SI: Serial input SO: Serial output SB0, SB1: Serial bus SCK: Serial clock

PWM0, PWM1: Pulse width modulation output

WDTO: Watchdog timer output

MODE0, MODE1: Mode

AD0-AD7: Address/data bus A8-A15: Address bus ASTB: Address strobe RD: Read strobe WR: Write strobe RESET: Reset

X1, X2: Crystal AVDD: Analog VDD AVss: Analog Vss

AVREF: Analog reference voltage

VDD: Power supply

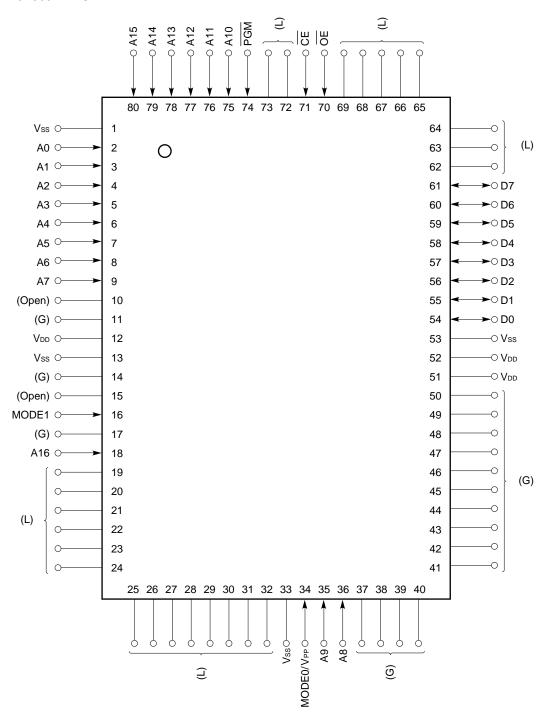
Vss: Ground

IC: Internally connected



(2) PROM programming mode (MODE0/VPP = H, MODE1 = L)

- 80-pin plastic QFP (14 \times 20 mm) μ PD78P368AGF-3B9
- 80-pin ceramic WQFN μPD78P368AKL-S



Caution Symbols in parentheses denote how the pins not used in the PROM programming mode should be treated.

- L: Connect these pins to the Vss pins through separate resistors.
- G: Connect these pins to the Vss pins.

Open: Do not connect these pins to anything.

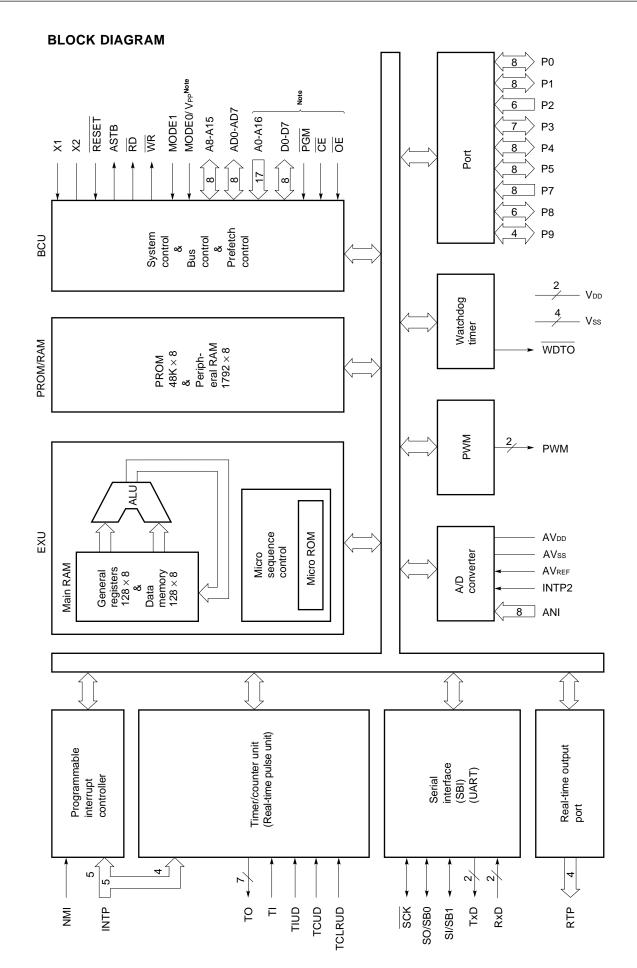
NEC μ PD78P368A

A0-A16: Address bus MODE0, MODE1: Programming mode set D0-D7: Data bus VPP: Programming power supply

CE:Chip enableVDD:Power supplyOE:Output enableVss:Ground

PGM: Programming mode





Note Shading indicates the pins used in the PROM programming mode.



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1. PIN FUNCTIONS

1.1 NORMAL OPERATION MODE (MODE0 = L, MODE1 = L)

(1) Port pins

Pin name	I/O	Function	Dual-function pin
P00-P03	I/O	Port 0.	RTP0-RTP3
P04		8-bit I/O port.	PWM0
P05		Can be specified as input or output bit by bit.	TCUD/PWM1
P06			TIUD/TO40
P07			TCLRUD
P10-P17	I/O	Port 1. 8-bit I/O port. Can be specified as input or output bit by bit.	-
P20	1	Port 2.	NMI
P21		Port used only for 6-bit input.	INTP0
P22			INTP1
P23			INTP2
P24			INTP3/TI
P25			INTP4
P30	I/O	Port 3.	TxD0
P31		7-bit I/O port.	RxD0
P32		Can be specified as input or output bit by bit.	SO/SB0
P33			SI/SB1
P34			SCK
P35			TxD1
P36			RxD1
P40-P47	I/O	Port 4. 8-bit I/O port. Can be specified as input or output in units of 8 bits.	AD0-AD7
P50-P57	I/O	Port 5. 8-bit I/O port. Can be specified as input or output bit by bit.	A8-A15
P70-P77	I	Port 7. Port used only for 8-bit input.	ANI0-ANI7
P80-P85	I/O	Port 8. 6-bit I/O port. Can be specified as input or output bit by bit.	TO00 - TO05
P90	I/O	Port 9.	RD
P91		4-bit I/O port.	WR
P92		Can be specified as input or output bit by bit.	_
P93			_



(2) Non-port pins (1/2)

Pin name	I/O	Function	Dual-function pin
RTP0-RTP3	0	Outputs a pulse in real time as triggered by a trigger signal sent from the real-time pulse unit.	P00-P03
NMI	I	Nonmaskable interrupt request input	P20
INTP0		External interrupt request input	P21
INTP1			P22
INTP2			P23
INTP3			P24/TI
INTP4			P25
TI	1	External count clock input to timer 1	P24/INTP3
TCUD		Input for the control signal to determine whether the up/down counter (timer 4) counts up or down.	P05/PWM1
TIUD		External count clock input to the up/down counter (timer 4)	P06/TO40
TCLRUD		Clear signal input to the up/down counter (timer 4)	P07
TO00-TO05	0	Pulse output from the real-time pulse unit	P80-P85
TO40			P06/TIUD
ANI0-ANI7	I	Analog input to the A/D converter	P70-P77
TxD0	0	Serial data output from the asynchronous serial interface	P30
TxD1			P35
RxD0	I	Serial data input to the asynchronous serial interface	P31
RxD1			P36
SCK	I/O	Serial clock I/O for the clock synchronous serial interface	P34
SI	I	Serial data input to the clock synchronous serial interface in the 3-wire mode	P33/SB1
so	0	Serial data output from the clock synchronous serial interface in the 3-wire mode	P32/SB0
SB0	I/O	Serial data I/O for the clock synchronous serial interface in the SBI mode	P32/SO
SB1			P33/SI
PWM0	0	PWM signal output	P04
PWM1			P05/TCUD
WDTO	0	Output for the signal which indicates the watchdog timer overflowed. (A nonmaskable interrupt is generated.)	-
AD0-AD7	I/O	Multiplexed address/data bus used when external memory is expanded	P40-P47
A8-A15		Address bus used when external memory is expanded	P50-P57
ASTB	0	Output for the timing signal used in externally latching address information output from the AD0 to AD7 and A8 to A15 pins, in order to access the external memory	-
RD		Read strobe signal output to the external memory	P90
WR		Write strobe signal output to the external memory	P91



(2) Non-port pins (2/2)

Pin name	I/O	Function	Dual-function pin
MODE0	1	Input for the control signal which sets the operation mode. Normally, both	-
MODE1		MODE0 and MODE1 are directly connected to the Vss pin.	
RESET	I	System reset input	_
X1	1	Crystal input pin for the system clock. A clock signal provided externally is	-
X2	_	input to the X1 pin. The reversed signal of the clock signal is input to the X2 pin.	
AVREF	I	A/D converter reference voltage input	-
AVDD	_	Analog power supply for the A/D converter	-
AVss	_	Ground for the A/D converter	_
V _{DD}	_	Positive power supply	-
Vss	_	Ground	-
IC	_	Internally connected. Directly connect the IC pin to Vss.	-

1.2 PROM PROGRAMMING MODE (MODE0/VPP = H, MODE1 = L)

Pin name	I/O	Function		
MODE0/Vpp	ı	PROM programming mode set/programming supply voltage		
MODE1	ı	PROM programming mode set		
A0-A16	ı	Address bus		
D0-D7	I/O	Data bus		
PGM	ı	Program input		
CE	I	Enable PROM		
ŌĒ	I	Read strobe to PROM		
V _{DD}	_	Positive power supply		
Vss		GND		



1.3 INPUT/OUTPUT CIRCUIT TYPE FOR EACH PIN AND HANDLING OF UNUSED PINS

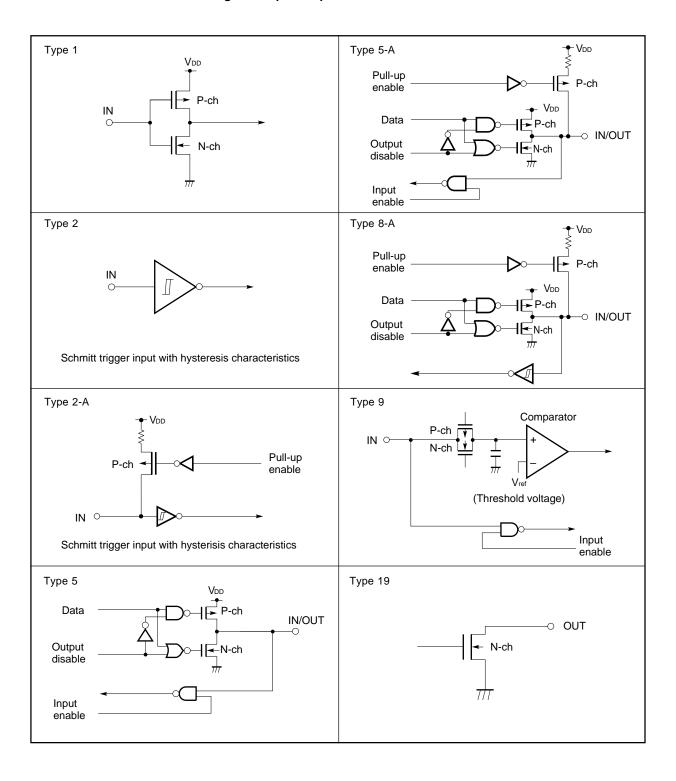
Table 1-1 lists the input and output circuit type for each pin and how to handle it when it is not used. Fig. 1-1 shows the circuits.

Table 1-1 Input/Output Circuit Type for Each Pin and Recommended Connection Methods for Unused Pins

Pin	I/O circuit type	Recommended connection method
P00/RTP0-P03/RTP3	5-A	Input state: Each pin is connected to the V _{DD} or
P04/PWM0		Vss pin via a separate resistor. Output state: Open
P05/TCUD/PWM1		Output state: Open
P06/TIUD/TO40		
P07/TCLRUD		
P10-P17		
P20/NMI	2	Connected to the Vss pin.
P21/INTP0	2-A	
P22/INTP1		
P23/INTP2		
P24/INTP3/TI		
P25/INTP4		
P30/TxD0	5-A	Input state: Each pin is connected to the VDD or
P31/RxD0		Vss pin via a separate resistor.
P32/SO/SB0	8-A	Output state: Open
P33/SI/SB1		
P34/SCK		
P35/TxD1	5-A	
P36/RxD1		
P40/AD0-P47/AD7		
P50/A8-P57/A15		
P70/ANI0-P77/ANI7	9	Connected to the Vss pin.
P80/TO00-P85/TO05	5-A	Input state: Each pin is connected to the V _{DD} or
P90/RD		Vss pin via a separate resistor.
P91/WR		Output state: Open
P92, P93		
ASTB	5	
WDTO	19	Connected to the Vss pin.
MODE0, MODE1	1	-
RESET	2	
AVREF, AVSS	_	Connected to the Vss pin.
AVDD		Connected to the VDD pin.



Fig. 1-1 Input/Output Circuits of Each Pin





2. MEMORY CONFIGURATION

The μ PD78P368A can access memory of up to 64K bytes. Fig. 2-1 shows the memory map.

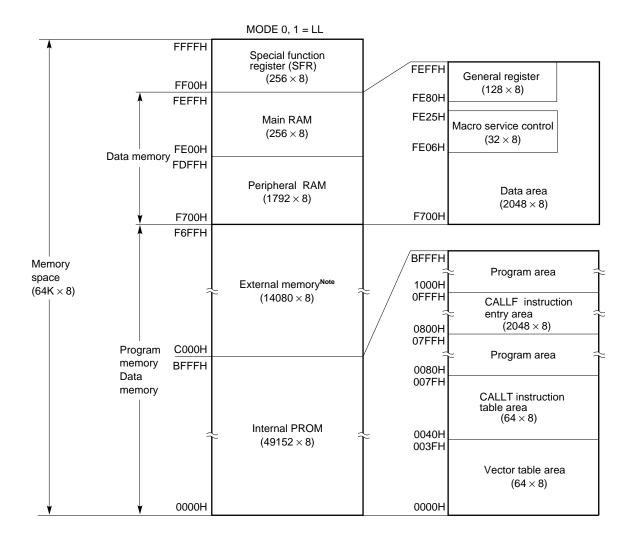


Fig. 2-1 Memory Map

Note Access in the external memory expansion mode.

Caution When word access (including the stack operation) to the main RAM space (FE00H to FEFFH) is executed, the addresses specified in the operand must be even numbers.



3. DIFFERENCES BETWEEN THE μ PD78P368A AND μ PD78366A

The μ PD78P368A is produced by replacing the internal mask ROM of the μ PD78366A with a 48K-byte PROM. Both have the same functions except some differences in ROM specifications, such as write and verify modes. Table 3-1 shows the differences.

In this manual, the functions specific to the μ PD78P368A are explained. For details of the other functions, refer to the μ PD78366A document.

Table 3-1 Differences between the μ PD78P368A and μ PD78366A

Part number Item	μPD78	μPD78366A			
ROM	48K bytes		32K bytes		
Internal program memory (Electrical write)	One-time PROM EPROM (Data can be (Data can be written once) written multiple times)		Mask ROM		
PROM programming pin	Provided	Not provided			
Setting of MODE0 and MODE1	Normal operation mode MODE0, 1 = LL PROM programming mode MODE0, 1 = HL	 Normal operation mode MODE0, 1 = LL ROM-less mode MODE0, 1 = HH 			
Package	80-pin plastic QFP 80-pin ceramic WQFN		80-pin plastic QFP		
Electrical characteristics	They differ in supply current and other factors.				
Others	Since each product has a different circuit scale and mask layout, the noise immunity and noise radiation of each product differ.				

- Cautions 1. The PROM and mask ROM products differ in noise immunity and noise radiation. Use not ES products but CS products (mask ROM products) to evaluate them thoroughly when considering the change from the PROM products to the mask ROM products during processes from preproduction to volume production.
 - 2. Connect the MODE0 and MODE1 pins directly to the VDD or Vss pin.



4. PROM PROGRAMMING

The μ PD78P368A is provided with an electrically writable PROM of 48K × 8 bits. When programming this PROM, use the MODE0/V_{PP} and MODE1 pins to set the μ PD78P368A to the PROM programming mode.

The μ PD78P368A provides programming characteristics compatibility with the μ PD27C1001A.

Table 4-1 Pin Functions in Programming Mode

Function	Normal operation mode Programming mod			
Address input	P00-P07, P21, P20, P80-P85, P30 A0-A16			
Data input	P40-P47	D0-D7		
Program pulse	ASTB	PGM		
Chip enable	P91 CE			
Output enable	P90 OE			
Program voltage	MODE0/V _{PP}			
Mode control	MODE1			

4.1 OPERATION MODE

To enter the program write/verify mode, set each pin as follows: MODE0/VPP = H, MODE1 = L. In addition, any of the operation modes listed in Table 4-2 can be selected by setting the $\overline{\text{CE}}$, $\overline{\text{OE}}$, and $\overline{\text{PGM}}$ pins in this mode.

Set the μ PD78P368A to the read mode in order to read the contents of PROM.

Handle unused pins as described in PIN CONFIGURATION (2).

Table 4-2 Operation Modes for PROM Programming

Mode	MODE1	CE	ŌE	PGM	MODE0/V _{PP}	V _{DD}	D0-D7
Page data latch	L	Н	L	Н	+12.5 V	+6.5 V	Data input
Page program		Н	Н	L			High impedance
Byte program		L	Н	L			Data input
Program verify		L	L	Н			Data output
Program inhibit		×	L	L			High impedance
		×	Н	Н			
Read		L	L	Н	+5 V	+5 V	Data output
Output disable		L	Н	×			High impedance
Standby		Н	×	×			High impedance

 $\textbf{Remark} \hspace{0.1cm} \times \hspace{-0.1cm} : \hspace{0.1cm} L \hspace{0.1cm} or \hspace{0.1cm} H$



4.2 PROCEDURE FOR WRITING ON PROM (PAGE PROGRAM MODE)

The following is a procedure for writing on PROM. (See Fig. 4-1.)

In the page program mode, data is written in units of pages (four bytes). When write data completes midway of a page, latch FFH after the data so that the data fits into pages.

- (1) Always set each pin as follows: MODE0/VPP = H and MODE1 = L. Connect unused pins according to PIN CONFIGURATION (2).
- (2) Apply +6.5 V to the VDD pin and +12.5 V to the VPP pin.
- (3) Input an initial address to the A0 to A16 pins.
- (4) Clear the page counter.
- (5) Data latch mode. Input write data to the D0 to D7 pins and input an active-low pulse to the \overline{OE} pin. Increment the address and the page counter.
- (6) Repeat step (5) for a page (four bytes).
- (7) Input a 0.1 ms program pulse (active low) to the PGM pin.
- (8) Verify mode. Checks if data has been written in PROM.

 Apply a low level to the \overline{CE} pin, input an active-low pulse to the \overline{OE} pin, and then read the write data from the D0 to D7 pins. Repeat this for a page (four bytes). When verification completes, apply a high level to the \overline{CE} pin.
 - If data has been written, go to step (10).
 - If not, repeat steps (7) and (8). If no data is written yet after the steps have been repeated 10 times, go to step (9).
- (9) Assume the device to be defective and stop write operation.
- (10) Increment the address.
- (11) Repeat steps (4) to (10) until the address exceeds the last address.

Fig. 4-2 is a timing chart of these steps (2) to (9).



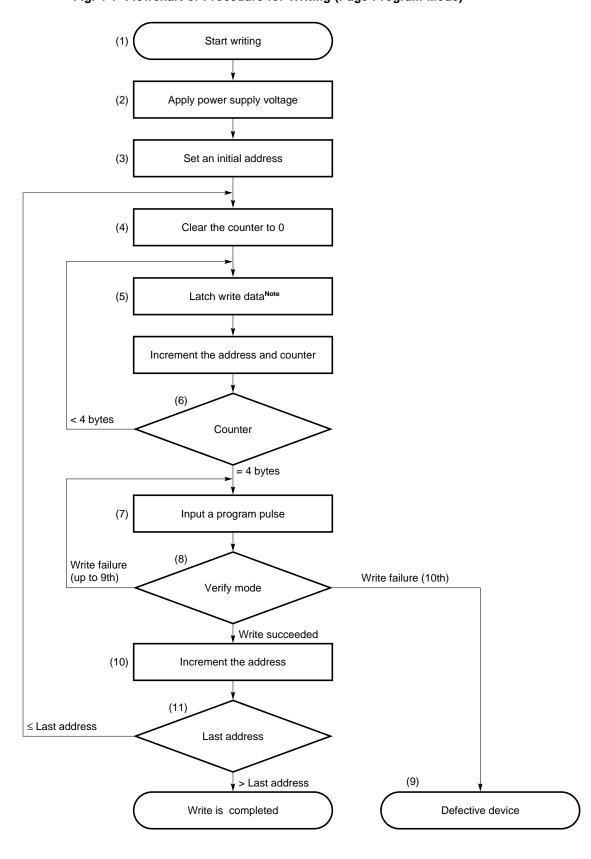


Fig. 4-1 Flowchart of Procedure for Writing (Page Program Mode)

Note If write data does not fill a page, latch FFH for the rest of the page.



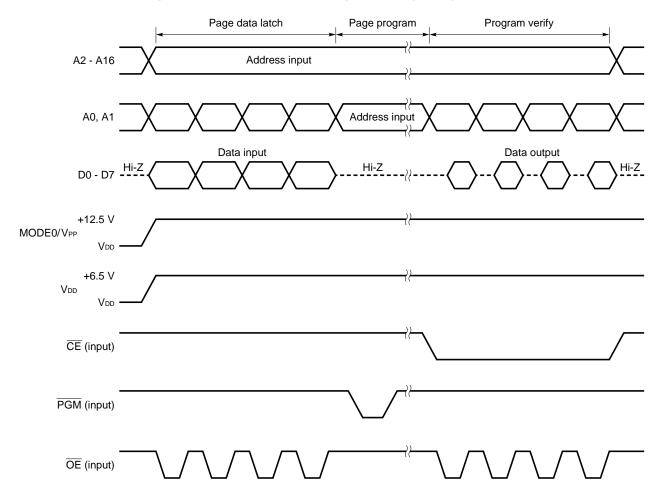


Fig. 4-2 PROM Write/Verify Timing Chart (Page Program Mode)

4.3 PROCEDURE FOR WRITING ON PROM (BYTE PROGRAM MODE)

The following is a procedure for writing on PROM. (See Fig. 4-3.)

- (1) Always set each pin as follows: MODE0/VPP = H and MODE1 = L. Connect unused pins according to PIN CONFIGURATION (2).
- (2) Apply +6.5 V to the VDD pin and +12.5 V to the MODE0/VPP pin, and input a low-level signal to the CE pin.
- (3) Input an initial address to the A0 to A16 pins.
- (4) Input write data to the D0 to D7 pins.
- (5) Input a 0.1 ms program pulse (active low) to the \overline{PGM} pin.
- (6) Verify mode. Checks if data has been written in PROM.
 - Input an active-low pulse to the \overline{OE} pin and read the write data from the D0 to D7 pins.
 - If data has been written, go to step (8).
 - If not, repeat steps (4) to (6). If no data is written yet after the steps have been repeated 10 times, go to step (7).
- (7) Assume the device to be defective and stop write operation.
- (8) Increment the address.
- (9) Repeat steps (4) to (8) until the address exceeds the last address.

Fig. 4-4 is a timing chart of these steps (2) to (7).

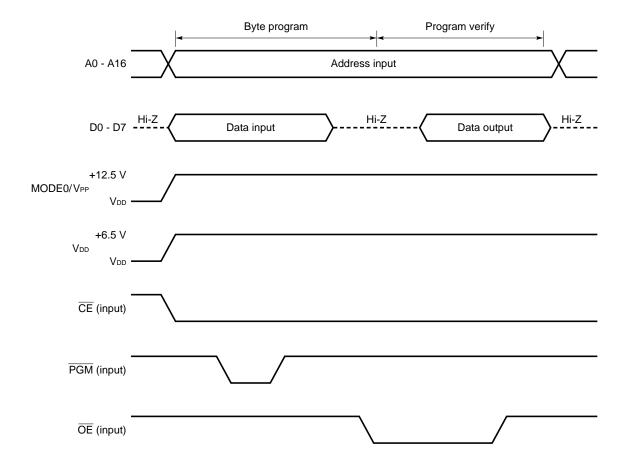


(1) Start writing Apply power supply voltage (3) Set an initial address (4) Input write data Input a program pulse (6) Write failure (up to 9th) Write failure (10th) Verify mode Write succeeded (8) Increment the address (9) ≤ Last address Last address (7) > Last address Write is completed Defective device

Fig. 4-3 Flowchart of Procedure for Writing (Byte Program Mode)



Fig. 4-4 PROM Write/Verify Timing Chart (Byte Program Mode)





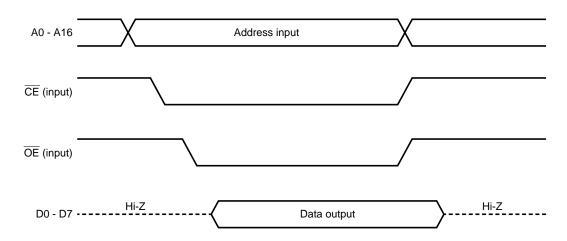
4.4 PROCEDURE FOR READING FROM PROM

The following is a procedure for reading out the contents of PROM to the external data bus (D0 to D7).

- (1) Always set each pin as follows: MODE0/VPP = H and MODE1 = L. Connect unused pins according to PIN CONFIGURATION (2).
- (2) Apply +5 V to the VDD and MODEO/VPP pins.
- (3) Input the address of data to be read into the A0 to A16 pins.
- (4) Read mode ($\overline{CE} = L$, $\overline{OE} = L$)
- (5) Output the data on the D0 to D7 pins.

Fig. 4-5 is a timing chart of these steps (2) to (5).

Fig. 4-5 PROM Read Timing Chart





5. ERASURE CHARACTERISTICS (μPD78P368AKL-S ONLY)

Data written in the μ PD78P368AKL-S program memory can be erased (FFH); therefore users can write other data in the memory.

To erase the written data, expose the erasure window to light with a wavelength shorter than approx. 400 nm. Normally, ultraviolet light with a wavelength of 254 nm is employed. The amount of light required to completely erase the data is as follows:

- Intensity of ultraviolet light × erasing time: 15 W•s/cm² min.
- Erasing time: 15 to 20 minutes (When using a 12,000 μW/cm² ultraviolet lamp. It may, however, take more time due to lamp deterioration, dirt on the erasure window, or the like.)

The ultraviolet lamp should be placed within 2.5 cm from the erasure window during erasure. In addition, if a filter is attached to the ultraviolet lamp, remove the filter before erasure.

6. PROTECTIVE FILM COVERING THE ERASURE WINDOW (μPD78P368AKL-S ONLY)

After the erasure window of the μ PD78P368AKL-S has been exposed to sunlight or a fluorescent lamp for a long time, data in EPROM may be erased and the internal circuits may malfunction. To prevent these failures, the erasure window should be covered with a protective film when it is not used for erasure.

EPROM package products with a window are supplied with a NEC-guaranteed protective film when they are delivered.

7. SCREENING ONE-TIME PROM PRODUCTS

NEC cannot execute a complete test of one-time PROM products (μ PD78P368AGF-3B9) due to their structure before shipment. It is recommended that you screen (verify) PROM products after writing necessary data into them and storing them at 125 °C for 24 hours.

NEC offers a charged service called QTOP microcomputer service. This service includes writing to one-time PROM, marking, screening, and verification. Ask your sales representative for details.



8. ELECTRICAL SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

Parameter	Symbol	Conditions	Rating	Unit
Power supply voltage	V _{DD}		-0.5 to +7.0	V
	AVDD		-0.5 to V _{DD} + 0.5	V
	VPP		-0.5 to +13.5	V
	AVss		-0.5 to +0.5	V
Input voltage	Vı	Pins other than P70/ANI0-P77/ANI7	-0.5 to V _{DD} + 0.5	V
Output voltage	Vo		-0.5 to V _{DD} + 0.5	V
Low-level output current	Іоь	Note	20	mA
		Output pins other than those in the note	4.0	mA
		Total of all output pins	200	mA
High-level output current	Іон	All output pins	-3.0	mA
		Total of all output pins	-25	mA
Analog input voltage	VIAN	P70/ANI0-P77/ANI7 pins	AVss - 0.5 to AVDD + 0.5	V
A/D converter reference input voltage	AVREF		AVss - 0.5 to AVDD + 0.5	V
Operating ambient temperature	Та		-40 to +85	°C
Storage temperature	T _{stg}		-60 to +150	°C

Note P00/RTP0-P03/RTP3, P04/PWM0, P05/TCUD/PWM1, P06/TIUD/TO40, P07/TCLRUD, P10-P17, and P80/TO00-P85/TO05 pins.

Caution Absolute maximum ratings are rated values beyond which some physical damages may be caused to the product; if any of the parameters in the table above exceeds its rated value even for a moment, the quality of the product may deteriorate. Be sure to use the product within the rated values.

RECOMMENDED OPERATING CONDITIONS

Oscillation frequency	TA	V _{DD}
3 MHz - fxx - 8 MHz	−40 to +85 °C	+5.0 V ±10 %

CAPACITANCE (TA = 25 °C, Vss = VDD = 0 V)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input capacitance	Cı	f = 1 MHz			20	pF
Output capacitance	Со	0 V except measured pins			20	pF
I/O capacitance	Сю				20	pF



OSCILLATOR CHARACTERISTICS ($T_A = -40 \text{ to } +85 \text{ °C}$, $V_{DD} = +5 \text{ V} \pm 10 \text{ %}$, $V_{SS} = 0 \text{ V}$)

Resonator	Recommended circuit	Parameter	Min.	Max.	Unit
Ceramic resonator or crystal	Vss X1 X2 C1 — C2	Oscillation frequency (fxx)	3	8	MHz
External clock	1 1	X1 input frequency (fx)	3	8	MHz
	X1 X2 Open	X1 rise/fall time (txR, txF)	0	30	ns
	HCMOS inverter	X1 input high-/low-level width (twxH, twxL)	40	170	ns

Caution When using system clock oscillation circuits, to reduce the effect of the wiring capacitance, etc, wire the area indicated by dotted-line as follows:

- Make the wiring as short as possible.
- Do not allow the wiring to intersect other signal lines. Keep it away from other lines in which varying high currents flow.
- Make sure that the ground point of the oscillation circuit capacitor is always at the same electric
 potential as Vss. Do not allow the wiring to be grounded to a ground pattern in which very high
 currents are flowing.
- Do not extract signals from the oscillation circuit.



DC CHARACTERISTICS ($T_A = -40 \text{ to } +85 \text{ °C}$, $V_{DD} = +5 \text{ V } \pm 10 \text{ %}$, $V_{SS} = 0 \text{ V}$)

Parameter	Symbol		Conditions	Min.	Тур.	Max.	Unit
Low-level input voltage	V _{IL1}	Note 1		0		0.8	V
	V _{IL2}	Note 2	Note 2			0.2V _{DD}	V
High-level input voltage	V _{IH1}	Note 1		2.2			V
	V _{IH2}	Note 2	Note 2 0				V
Low-level output voltage	V _{OL1}	Note 3	Note 3 IoL = 2.0 mA			0.45	V
	V _{OL2}	Note 4	lote 4 IoL = 15 mA			1.5	V
	Vol3	Note 5	IoL = 10 mA			1.5	V
High-level output voltage	Vон	Іон = -400 μΑ		V _{DD} - 1.0			V
Input leakage current	ILI	0 V - Vı - VDD	, AVDD = VDD			±10	μΑ
Output leakage current	Іьо	0 V - Vo - VD	o, AVDD = VDD			±10	μΑ
V _{DD} supply current	I _{DD1}	Operating mod	de		70	120	mA
	I _{DD2}	HALT mode			45	70	mA
Data retention voltage	VDDDR	STOP mode		2.5			V
Data retention current	Idddr	STOP mode V _{DDDR} = 2.5 V			2	10	μΑ
			VDDDR = 5.0 V ±10 %		10	50	μΑ
Pull-up resistance	R∟	V1 = 0 V		15	60	150	Κý

Notes 1. Pins other than those specified in Note 2.

- **2.** RESET, X1, X2, P20/NMI, P21/INTP0, P22/INTP1, P23/INTP2, P24/INTP3/TI, P25/INTP4, P32/SO/SB0, P33/SI/SB1 and P34/SCK pins.
- 3. Pins other than those specified in Notes 4 and 5.
- **4.** P80/T000-P85/T005 pins (When IoL = 15 mA is in operation, up to three pins can be ON simultaneously.)
- 5. P00/RTP0-P03/RTP3, P04/PWM0, P05/TCUD/PWM1, P06/TIUD/TO40 and P07/TCLRUD pins (When IoL = 10 mA is in operation, up to four pins can be ON simultaneously.) as well as P10-P17 pins (When IoL = 10 mA is in operation, up to four pins can be ON simultaneously.).

Caution When the P80-P85, P00-P07, and P10-P17 pins are not used under the conditions specified in Notes 4 and 5, they have the same characteristics as in Note 3.



AC CHARACTERISTICS (TA = -40 to +85 °C, VDD = +5 V ± 10 %, Vss = 0 V, CL = 100 pF, fxx = 8 MHz)

Read/Write Operation (when general-purpose memory is connected)

Parameter	Symbol	Conditions	Min.	Max.	Unit
System clock cycle time	t cyk		62.5	166.7	ns
Address setup time (vs. ASTB ↓)	t sast		7		ns
Address hold time (vs. ASTB ↓)	t HSTA		11		ns
$\overline{RD} \downarrow o$ address float time	tfra			24	ns
Address → data input time	tdaid			100	ns
$\overline{RD} \downarrow \to data$ input time	t DRID			49	ns
$ASTB \downarrow \to \overline{RD} \downarrow delay \ time$	t DSTR		15		ns
Data hold time (vs. RD ∞)	thrid		0		ns
$\overline{\text{RD}} \infty \to \text{address active time}$	tdra		17		ns
RD low-level width	twrl		63		ns
ASTB high-level width	twsтн		14		ns
$\overline{ m WR} \downarrow ightarrow$ data output time	towod			21	ns
$ASTB \downarrow \to \overline{WR} \downarrow delay \; time$	t DSTW		15		ns
$\overline{WR} {\scriptstyle{\otimes}} {\rightarrow} ASTB {\scriptstyle{\otimes}} delay \; time$	towst		78		ns
Data setup time (vs. WR ∞)	tsodw		57		ns
Data hold time (vs. WR ∞)	thwod		8		ns
WR low-level width	twwL		63		ns

tcγκ-dependent Bus Timing Definition

Parameter	Arithmetic expression	Min./Max.	Unit
tsast	(0.5 + a) T – 24	Min.	ns
thsta	0.5T - 20	Min.	ns
twsтн	(0.5 + a) T – 17	Min.	ns
tostr	0.5T – 16	Min.	ns
twrl	(1.5 + n) T – 30	Min.	ns
t daid	(2.5 + a + n) T – 56	Max.	ns
torio	(1.5 + n) T – 44	Max.	ns
tdra	0.5T – 14	Min.	ns
tostw	0.5T – 16	Min.	ns
towst	1.5T – 15	Min.	ns
twwL	(1.5 + n) T – 30	Min.	ns
towod	0.5T – 10	Max.	ns
tsodw	(1 + n) T – 5	Min.	ns

Remarks 1. T = tcyk = 1/fck (fck refers to the internal system clock frequency.)

- 2. a becomes 1 when the address wait is inserted. Otherwise, it becomes 0.
- 3. n refers to the number of wait cycles that is inserted by specifying the PWC register.
- 4. Only the bus timings indicated in this table depend on tcyk.



SERIAL OPERATION (TA = -40 to +85 °C, V_{DD} = +5 V ± 10 %, Vss = 0 V)

Parameter	Symbol	Conc	ditions	Min.	Max.	Unit
Serial clock cycle time	tcysk	SCK output	Internal 8 dividing	500		ns
		SCK input	External clock	500		ns
Serial clock low-level width	twskL	SCK output Internal 8 dividing		210		ns
		SCK input	External clock	210		ns
Serial clock high-level width	twsкн	SCK output	Internal 8 dividing	210		ns
		SCK input	External clock	210		ns
SI setup time (vs. SCK ∞)	tsrxsk			80		ns
SI hold time (vs. SCK ∞)	thskrx			80		ns
$\overline{SCK} \downarrow \to SO$ delay time	tosktx	R = 1 ký, C = 100 pF		210	ns	

UP/DOWN COUNTER OPERATION (TA = -40 to +85 °C, VDD = +5 V ± 10 %, Vss = 0 V)

Parameter	Symbol	Conditions	Min.	Max.	Unit
TIUD high-/low-level width	twтiuн, twтiuL	Other than mode 4	2T		ns
		Mode 4	4T		ns
TCUD high-/low-level width	twтcuн, twтcuL	Other than mode 4	2T		ns
		Mode 4	4T		ns
TCLRUD high-/low-level width	twcluh, twclul		2T		ns
TCUD setup time (vs. TIUD ∞)	t stcu	Mode 3	Т		ns
TCUD hold time (vs. TIUD ∞)	tнтси	Mode 3	Т		ns
TIUD setup time (vs. TCUD)	t s4TIU	Mode 4	2T		ns
TIUD hold time (vs. TCUD)	t н4тіи	Mode 4	2T		ns
TIUD & TCUD cycle time	tcyc	Other than mode 4		4	MHz
	tcYC4	Mode 4		2	MHz

Remark T = tcyk = 1/fck (fck refers to the internal system clock frequency.)



OTHER OPERATIONS (TA = -40 to +85 °C, VDD = +5 V ± 10 %, Vss = 0 V)

Parameter	Symbol	Conditions	Min.	Max.	Unit
NMI high-/low-level width	twnih, twnil		2		μs
RESET high-/low-level width	twrsh, twrsl		1.5		μs
INTP0 high-/low-level width	twioh, twiol	Ts = T	250		ns
		Ts = 4T	1.0		μs
		Ts = 8T	2.0		μs
		Ts = 16T	4.0		μs
INTP1 high-/low-level width	twi1H, twi1L	Ts = T	250		ns
		Ts = 4T	1.0		μs
		Ts = 8T	2.0		μs
		Ts = 16T	4.0		μs
INTP2 high-/low-level width	twizh, twizl	Ts = T	250		ns
		Ts = 4T	1.0		μs
INTP3(TI) high-/low-level width	twish, twish	Ts = T	250		ns
		Ts = 4T	1.0		μs
		Ts = 8T	2.0		μs
		Ts = 16T	4.0		μs
		Ts = 64T	16.0		μs
		Ts = 128T	32.0		μs
		Ts = 256T	64.0		μs
INTP4 high-/low-level width	twi4H, twi4L	Ts = T	250		ns
		Ts = 4T	1.0		μs
		Ts = 8T	2.0		μs
		Ts = 16T	4.0		μs

Remarks 1. T = tcyk = 1/fclk (fclk refers to the internal system clock frequency.)

2. Ts refers to the input sampling frequency. INTP0-INTP4 can be selected to programmable.

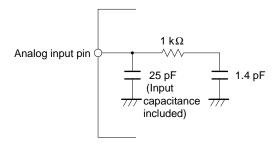


A/D CONVERTER CHARACTERISTICS ($T_A = -40 \text{ to } +85 \text{ °C}$, $V_{DD} = +5 \text{ V} \pm 10 \text{ %}$, $V_{SS} = AV_{SS} = 0 \text{ V}$, $V_{DD} - 0.5 \text{ V} - AV_{DD} - V_{DD}$)

Parameter	Symbol		Conditions	Min.	Тур.	Max.	Unit
Resolution				10			bit
Total errorNote 1		4.5 V - AVREF	- AV _{DD}			±0.4	%FSR
		3.4 V - AVREF	- AV _{DD}			±0.7	%FSR
Quantization error						±1/2	LSB
Conversion time	tconv	62.5 ns - tcүк	< 80 ns	208			t cyk
		80 ns - tсүк -	166.6 ns	169			t cyk
Sampling time	t SAMP	62.5 ns - tcүк	< 80 ns	8			t cyk
		80 ns - tсүк -	166.6 ns	6			t cyk
Zero-scale errorNote 1		4.5 V - AVREF	- AVDD		±1.5	±2.5	LSB
		3.4 V - AVREF	- AV _{DD}		±1.5	±4.5	LSB
Full-scale errorNote 1		4.5 V - AVREF	- AV _{DD}		±1.5	±2.5	LSB
		3.4 V - AVREF	- AV _{DD}		±1.5	±4.5	LSB
Nonlinearity errorNote 1		4.5 V - AVREF	- AV _{DD}		±1.5	±2.5	LSB
		3.4 V - AVREF	- AV _{DD}		±1.5	±4.5	LSB
Analog input voltageNote 2	VIAN			-0.3		AVREF + 0.3	V
Analog input impedance	RAN	When not sam	pling		10		МΩ
		When samplin	g		Note 3		
Reference voltage	AVREF			3.4		AV _{DD}	V
AVREF1 current	Alref				1.0	3.0	mA
AVDD supply current	Aldd	Operating mode			2.0	6.0	mA
A/D converter data	Aldddr	STOP mode	AVDDDR = 2.5 V		2	10	μΑ
retention current			AVDDDR = 5 V ±10 %		10	50	μΑ

Notes 1. The quantization error is excluded.

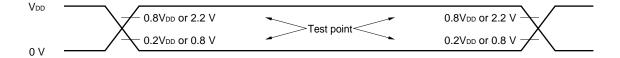
- 2. When $-0.3 \text{ V} \cdot \text{Vian} \cdot 0 \text{ V}$, the conversion result becomes 000H. When $0 \text{ V} \cdot \text{Vian} \cdot \text{AVREF}$, the conversion is performed with the 10-bit resolution. When AVREF Vian AVREF + 0.3 V, the conversion result becomes 3FFH.
- 3. The analog input impedance at the time of sampling is the same as the equivalent circuit shown below. (The values in the diagram are TYP. values; they are not guaranteed values.)





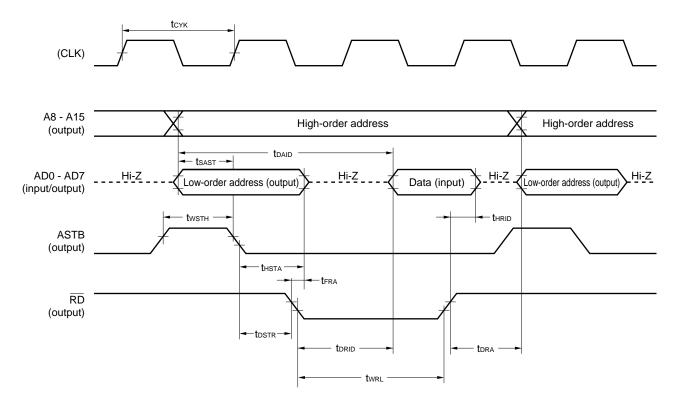
- Cautions 1. When using the P70/ANI0-P77/ANI7 pins for both digital and analog inputs, the previously described characteristics are not guaranteed. Therefore, ensure that all of the eight P70/ANI0-P77/ANI7 pins are used either for analog input or digital input.
 - 2. When using the P70/ANI0-P77/ANI7 pins as digital input, make sure to set that $AV_{DD} = V_{DD}$, and $AV_{SS} = V_{SS}$.

AC Timing Test Point

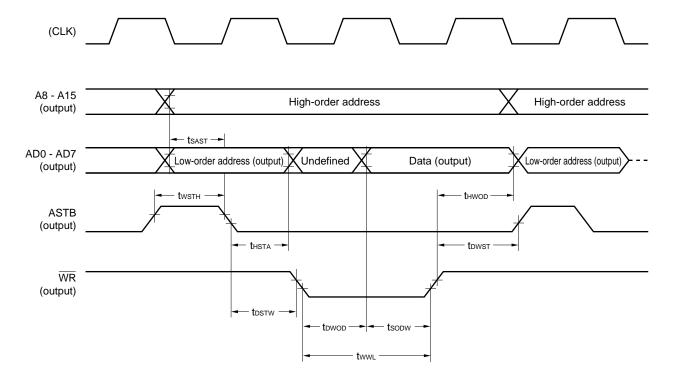




Read Operation

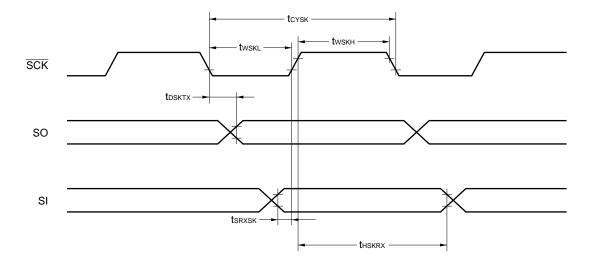


Write Operation

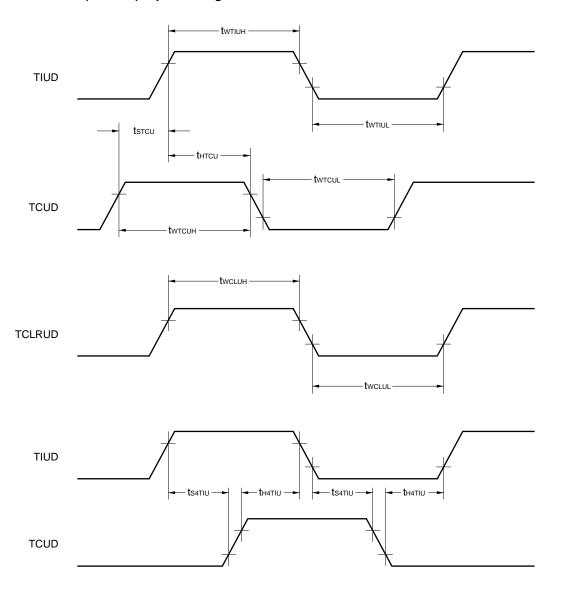




Serial Operation

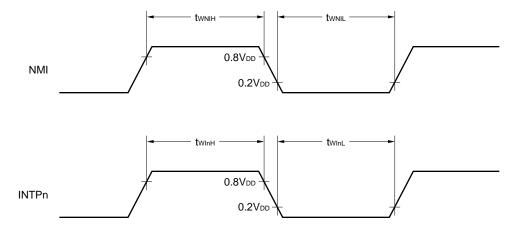


Up/Down Counter (Timer 4) Input Timing



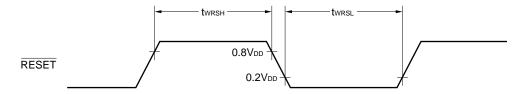


Interrupt Input Timing



Remark n = 0 - 4

Reset Input Timing





DC PROGRAMMING CHARACTERISTICS (TA = 25 ±5 °C, Vss = 0 V)

Parameter	Symbol	SymbolNote 1	Conditions	Min.	Тур.	Max.	Unit
High-level input voltage	Viн	Vıн		2.4		VDDP + 0.3	V
Low-level input voltage	VIL	VIL		-0.3		0.8	V
Input leakage current	ILIP	lu	0 - V _I - V _{DDP} Note 2			±10	μΑ
High-level output voltage	Vон	Vон	$I_{OH} = -400 \ \mu A$	2.4			V
Low-level output voltage	Vol	Vol	lo _L = 2.1 mA			0.45	V
Output leakage current	llo	-	0 - Vo - VDDP, OE = VIH			±10	μΑ
V _{DDP} supply voltage	VDDP	Vcc	Program memory write mode	6.25	6.5	6.75	V
			Program memory read mode	4.5	5.0	5.5	V
VPP supply voltage	V _{PP}	V _{PP}	Program memory write mode	12.2	12.5	12.8	V
			Program memory read mode	V _{DD} - 0.6	V _{DD}	V _{DD} + 0.6	V
VDDP supply current	ldd	IDD	Program memory write mode			50	mA
			Program memory read mode			50	mA
VPP supply current	I PP	IPP	Program memory write mode			50	mA
			Program memory read mode			100	μΑ

Notes 1. Symbols for the corresponding μ PD27C1001A

2. The V_{DDP} represents the V_{DD} pin as viewed in the programming mode.



AC PROGRAMMING CHARACTERISTICS (TA = 25 ±5 °C, Vss = 0 V)

PROM Write Mode (Page Program Mode)

Parameter	Symbol ^{Note 1}	Conditions	Min.	Тур.	Max.	Unit
Address set up time	tas		2			μs
CE set time	tces		2			μs
Input data setup time	tos		2			μs
Address hold time	tан		2			μs
	tahl		2			μs
	tahv		0			μs
Input data hold time	tон		2			μs
Output data hold time	tor		0		250	ns
V _{PP} setup time	tvps		1			ms
VDDP setup time	t _{VDS} Note 2		1			ms
Initial program pulse width	tpw		0.095		0.105	ms
OE set time	toes		2			μs
Valid data delay time from OE	toe				1.0	μs
OE pulse width in the data latch	tıw		1			μs
PGM setup time	tрымs		2			μs
CE hold time	tсен		2			μs
OE hold time	tоен		2			μs

Notes 1. These symbols (except tvps) correspond to those of the μ PD27C1001A.

2. For μ PD27C1001A, read tvps as tvcs.



PROM Write Mode (Byte Program Mode)

Parameter	Symbol ^{Note 1}	Conditions	Min.	Тур.	Max.	Unit
Address set up time	tas		2			μs
CE set time	tces		2			μs
Input data setup time	tos		2			μs
Address hold time	t ah		2			μs
Input data hold time	tон		2			μs
Output data hold time	tor		0		250	ns
V _{PP} setup time	tvps		1			ms
VDDP setup time	t _{VDS} Note 2		1			ms
Initial program pulse width	tpw		0.095		0.105	ms
OE set time	toes		2			μs
Valid data delay time from OE	toe				1.0	μs

Notes 1. These symbols (except tvps) correspond to those of the μ PD27C1001A.

2. For μ PD27C1001A, read tvps as tvcs.

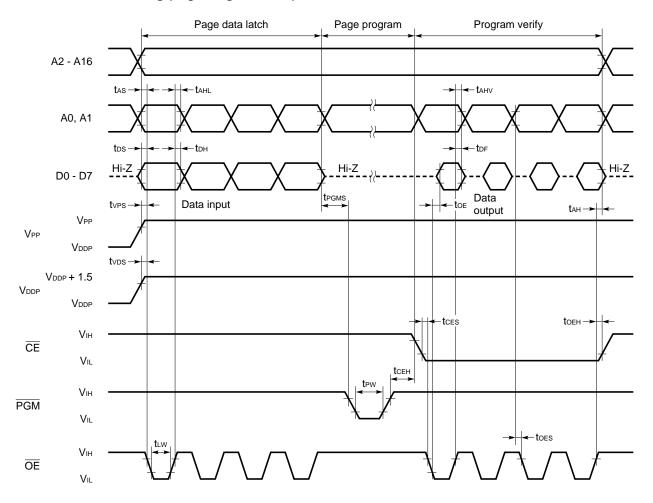
PROM Read Mode

Parameter	Symbol Note	Conditions	Min.	Тур.	Max.	Unit
Data output time from address	tacc	CE = OE = VIL			1.0	μs
$\overline{CE} \downarrow \to data$ output time	tce	OE = VIL			1.0	μs
$\overline{OE} \downarrow \to data$ output time	toe	CE = VIL			1.0	μs
Data hold time to OE ∞	tor	CE = VIL	0		250	ns
Data hold time to address	toн	CE = OE = VIL	0			ns

Note These symbols correspond to those of the μ PD27C1001A.

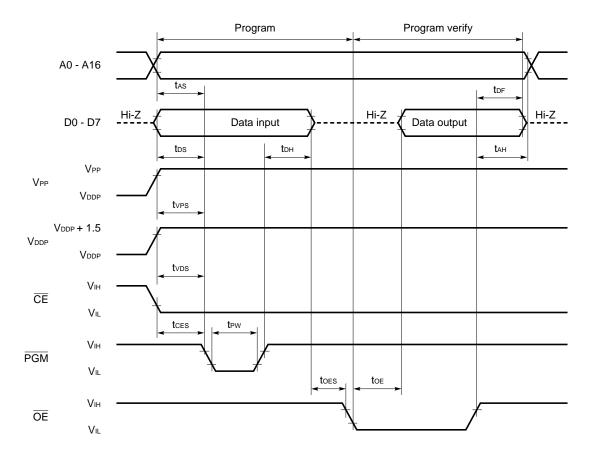


PROM Write Mode Timing (Page Program Mode)





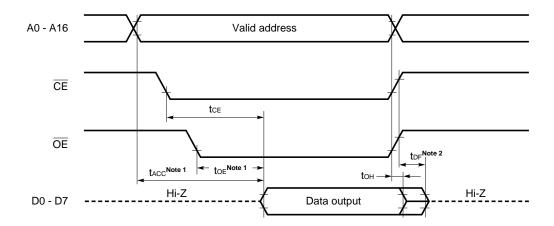
PROM Write Mode Timing (Byte Program Mode)



Cautions 1. VDDP must be applied before VPP, and must be cut after VPP.

- 2. VPP including overshoot must not exceed +13.5 V.
- 3. Plugging in or out the board with the VPP pin supplied with +12.5 V may adversely affect its reliability.

PROM Read Mode Timing

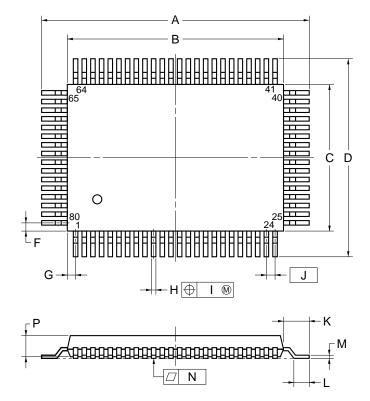


Notes 1. For reading within tacc, the delay of the \overline{OE} input from falling edge of \overline{CE} must be within tacc – toe.

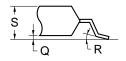
2. t_{DF} is the time measured from when either \overline{OE} or \overline{CE} reaches V_{IH} , whichever is faster.

9. PACKAGE DRAWINGS

80 PIN PLASTIC QFP (14×20)



detail of lead end



NOTE

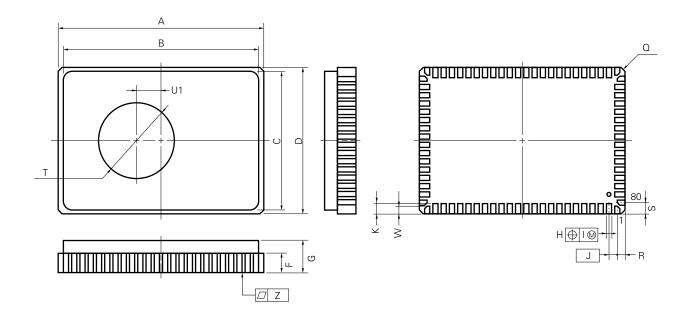
Each lead centerline is located within 0.15 mm (0.006 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
Α	23.6±0.4	0.929±0.016
В	20.0±0.2	$0.795^{+0.009}_{-0.008}$
С	14.0±0.2	$0.551^{+0.009}_{-0.008}$
D	17.6±0.4	0.693±0.016
F	1.0	0.039
G	0.8	0.031
Н	0.35±0.10	0.014+0.004
I	0.15	0.006
J	0.8 (T.P.)	0.031 (T.P.)
K	1.8±0.2	$0.071^{+0.008}_{-0.009}$
L	0.8±0.2	$0.031^{+0.009}_{-0.008}$
М	$0.15^{+0.10}_{-0.05}$	$0.006^{+0.004}_{-0.003}$
N	0.10	0.004
Р	2.7	0.106
Q	0.1±0.1	0.004±0.004
R	5°±5°	5°±5°
S	3.0 MAX.	0.119 MAX.

P80GF-80-3B9-3



80 PIN CERAMIC WQFN



NOTE

Each lead centerline is located within 0.08 mm (0.003 inch) of its true position (T.P.) at maximum material condition.

X80KW-80A1

ITEM	MILLIMETERS	INCHES
А	20.0±0.25	0.787 ^{+0.011} _{-0.010}
В	19.0	0.748
С	13.4	0.528
D	14.2±0.2	0.559±0.008
F	1.84	0.072
G	3.56MAX.	0.141MAX.
Н	0.51±0.1	0.02±0.004
I	0.08	0.003
J	0.8 (T.P.)	0.031 (T.P.)
K	1.0±0.15	0.039+0.007
Q	C0.3	C0.012
R	0.8	0.031
S	1.1	0.043
Т	φ7.62	φ0.3
U1	2.6	0.102
W	0.75±0.15	0.03+0.006
Z	0.10	0.004



10. RECOMMENDED SOLDERING CONDITIONS

These products should be soldered and mounted under the conditions recommended below.

For details of recommended soldering conditions, refer to the information document *Semiconductor Device Mounting Technology Manual* (C10535J).

For soldering methods and conditions other than those recommended, please contact your NEC sales representative.

Table 10-1. Surface Mount Type Soldering Conditions

 μ PD78P368AGF-3B9: 80-Pin Plastic QFP (14 \times 20 mm)

Soldering method	Soldering conditions	Recommended condition symbol
Infrared reflow	Package peak temperature: 235 °C, Duration: 30 sec. max. (210 °C or above) Number of times: 2 max. Exposure limit: 7 daysNote (20 hours of pre-baking is required at 125 °C afterward) <caution> Non-heat-resistant trays, such as magazine and taping trays, cannot be baked before unpacking.</caution>	IR35-207-2
VPS	Package peak temperature: 215 °C, Duration: 40 sec. max. (200 °C or above) Number of times: 2 max. Exposure limit: 7 daysNote (20 hours of pre-baking is required at 125 °C afterward) <caution> Non-heat-resistant trays, such as magazine and taping trays, cannot be baked before unpacking.</caution>	VP15-207-2
Wave soldering	Solder bath temperature: 260 °C or less, Time: 10 sec. max., Number of times: 1, Pre-heating temperature: 120 °C max. (Package surface temperature) Exposure limit: 7 days Note (20 hours of pre-baking is required at 125 °C afterward)	WS60-207-1
Partial heating	Pin temperature: 300 °C or less Duration: 3 sec. max. (per side of device)	-

Note Maximum number of days during which the product can be stored at a temperature of 25 °C and a relative humidity of 65 % or less after dry-pack package is opened.

Caution Use of more than one soldering method should be avoided (except in the case of partial heating).



APPENDIX A TOOLS

A.1 DEVELOPMENT TOOLS

The following tools are provided for developing a system that uses the μ PD78P368A:

Language processor

78K/III series relocatable assembler (RA78K3)	macro functions, A structured-prog description of pro	it allows the user t gramming assembl	ned for all 78K/III series of o improve program develor is also provided, whith ures. This assembler continuents.	elopment efficiency.		
	Host machine	os	Distribution media	Part number		
	PC-9800 series	MS-DOS TM	3.5-inch 2HD	μS5A13RA78K3		
			5.25-inch 2HD	μS5A10RA78K3		
	IBM PC/ATTM or	PC DOSTM	3.5-inch 2HC	μS7B13RA78K3		
	compatibles		5.25-inch 2HC	μS7B10RA78K3		
	HP9000 series	HP-UXTM	DAT	μS3P16RA78K3		
	SPARCstationTM	SunOS TM	Cartridge tape	μS3K15RA78K3		
	NEWSTM	NEWS-OSTM	(QIC-24)	μS3R15RA78K3		
78K/III series C compiler (CC78K3)	converts program	This C compiler can be used for all 78K/III series emulators. The compiler converts programs written in C language into object codes executable on the microcomputer. When the compiler is used, the 78K/III series relocatable assembler package (RA78K3) is needed.				
	Host machine	Host machine		Part number		
		OS	Distribution media			
	PC-9800 series	MS-DOS	3.5-inch 2HD	μS5A13CC78K3		
			5.25-inch 2HD	μS5A10CC78K3		
		PC DOS	3.5-inch 2HC	μS7B13CC78K3		
	compatibles		5.25-inch 2HC	μS7B10CC78K3		
	HP9000 series 700	HP-UX	DAT	μS3P16CC78K3		
	SPARCstation	SunOS	Cartridge tape	μS3K15CC78K3		
	NEWS	NEWS-OS	(QIC-24)	μS3R15CC78K3		

Remark It is guaranteed that the relocatable assembler and C compiler run only under the OSs on the corresponding host machines described above.



PROM programming tools

Hardware	PG-1500	optional program	The PG-1500 PROM programmer is used together with an accessory board and optional program adapter. It allows the user to program a single chip microcomputer containing PROM independently or from a host machine. The PG-1500 can be used to program typical 256K-bit to 4M-bit PROMs.			
	PA-78P368GF PA-78P368KL	PROM programm PA-78P368GF :	Programmer adapter for writing programs to the μ PD78P368A. Used with a PROM programmer such as the PG-1500. PA-78P368GF: For μ PD78P368AGF PA-78P368KL: For μ PD78P368AKL			
Software	PG-1500 controller	This program enables the host machine to control the PG-1500 through the seand parallel interfaces.			0 through the serial	
		Host machine	OS	Distribution media	- Part number	
		PC-9800 series	MS-DOS	3.5-inch 2HD	μS5A13PG1500	
				5.25-inch 2HD	μS5A10PG1500	
		IBM PC/AT or	PC DOS	3.5-inch 2HC	μS7B13PG1500	
		compatibles		5.25-inch 2HC	μS7B10PG1500	

Remark It is guaranteed that the PG-1500 controller runs only under the OSs on the corresponding host machines described above.

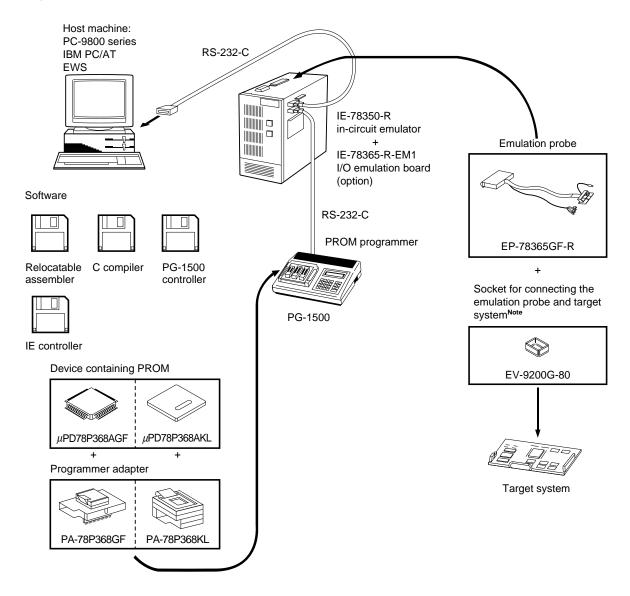
Debugging tools (when the IE controller is used)

Hardware	IE-78350-R		In-circuit emulator for developing and debugging an application system. For debugging, connect the emulator to the host machine.			
	IE-78365-R-EM1		I/O emulation board for emulating peripheral hardware such as the I/O ports of the target device.			
	EP-78365GF-R EV-9200G-80		Emulation probe for connecting the IE-78350-R to the target system. One EV-9200G-80 conversion socket is provided for connection to the target system.			
Software	IE-78350-R control program (IE controller)		1 ' '		er to control the IE-7835 execution function ensu	
			Host machine			Part number
			Tiost machine	os	Distribution media	T dit Hamber
			PC-9800 series	MS-DOS	3.5-inch 2HD	μS5A13IE78365A
					5.25-inch 2HD	μS5A10IE78365A
			IBM PC/AT or	PC DOS	3.5-inch 2HC	μS7B13IE78365A
			compatibles		5.25-inch 2HC	μS7B10IE78365A

Remark It is guaranteed that the IE controller runs only under the OSs on the corresponding host machines described above.



Configuration of development tools (when the IE controller is used)



Note The socket is supplied with the emulation probe.

Remarks 1. The PG-1500 can be directly connected to the host machine via the RS-232-C interface.

2. In this figure, the distribution media of software is represented by the 3.5-inch floppy disk.



Debugging tools (when the integrated debugger is used)

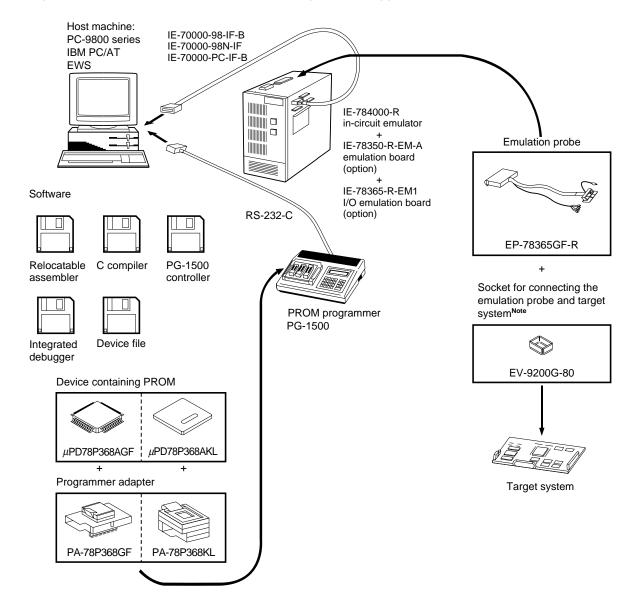
Hardware	IE-784000-R		In-circuit emulator for developing and debugging an application system. For debugging, connect the emulator to the host machine.					
	IE-78350-R-EM-ANote		Emulation board for e target device.	Emulation board for emulating peripheral hardware such as the I/O ports of the target device.				
	IE-7836	5-R-EM1	I/O emulation board for the target device.	or emulating pe	ripheral hardware such a	s the I/O ports of		
	EP-7836	65GF-R EV-9200G-80	Emulation probe for connecting the IE-784000-R to the target system. One EV-9200G-80 conversion socket is provided for connection to the target system.					
	IE-7000	0-98-IF-B	Interface adapter whe used as the host mac		series computer (other th	ian a notebook) is		
	IE-7000	0-98N-IF	Interface adapter and machine.	cable when a l	PC-9800 series notebook	is used as the host		
	IE-7000	0-PC-IF-B	Interface adapter whe	n the IBM PC/A	AT is used as the host ma	achine.		
	IE-7800	0-R-SV3	Interface adapter and	cable when the	e EWS is used as the hos	st machine.		
Software	Integrate (ID78K3	ed debugger	_	•	emulator for the 78K/III se			
		assembly language, o	Debugging can be performed for the source program written in C, structured assembly language, or assembly language. The ID78K3 can display various information simultaneously on the host machine screen divided into multiple areas. This ensures efficient debugging.					
			Host machine	OS	Distribution media	Part number		
			PC-9800 series	MS-DOS	3.5-inch 2HD	μSAA13ID78K3		
				+ Windows TM	5.25-inch 2HD	μSAA10ID78K3		
			IBM PC/AT or	PC DOS	3.5-inch 2HC	μSAB13ID78K3		
			compatibles (Japanese Windows)	Windows	5.25-inch 2HC	μSAB10ID78K3		
	Device file (DF78365)		IBM PC/AT or		3.5-inch 2HC	μ SBB13ID78K3		
			compatibles (Windows)		5.25-inch 2HC	μSBB10ID78K3		
			File which contains the device-specific information. The device file (DF78365) is used together with the assembler (RA78K3), C compiler (CC78K3), or integrated debugger (ID78K3).					
			Host machine	os	Distribution media	Part number		
			PC-9800 series	MS-DOS	3.5-inch 2HD	μS5A13DF78365		
					5.25-inch 2HD	μS5A10DF78365		
			IBM PC/AT or	PC DOS	3.5-inch 2HC	μS7B13DF78365		
			compatibles		5.25-inch 2HC	μS7B10DF78365		

Note Under development

Remark It is guaranteed that the integrated debugger and device file run only under the OSs on the corresponding host machines described above.



Configuration of development tools (when the integrated debugger is used)



Note The socket is supplied with the emulation probe.

Remarks 1. In this figure, the host machine is represented by the desktop personal computer.

2. In this figure, the distribution media of software is represented by the 3.5-inch floppy disk.



A.2 EMBEDDED SOFTWARE

To improve the efficiency of program development and simplify the maintenance of systems incorporating this microcontroller, the following embedded software is provided.

Real-time OS

Real-time OS (RX78K/III)Note	This operating system was designed to provide a multitasking environment for control applications that require real-time processing. System performance is improved by using the idling CPU for other processing. RX78K/III provides system calls that conform to μ ITRON specifications. The RX78K/III package provides the RX78K/III nucleus and a tool (Configurator) that is used for creating multiple information tables.			
	Host machine	Distribution media	Part number	
	PC-9800 series	MS-DOS	3.5-inch 2HD	Undecided
			5.25-inch 2HD	Undecided
	IBM PC/AT or	PC DOS	3.5-inch 2HC	Undecided
	compatibles		5.25-inch 2HC	Undecided

Note Under development

Caution Before purchasing this software, complete the purchase application sheet and sign the software license agreement.

Remark To use the RX78K/III real-time operating system, the optional RA78K3 assembler package is required.



Fuzzy inference development support system

Tool for creating fuzzy knowledge data (FE9000, FE9200)	This program supports the input/editing and simulation of fuzzy knowledge data (fuzzy rules and membership functions).				
•	Host machine	os	Distribution media	Part number	
	PC-9800 series	MS-DOS	3.5-inch 2HD	μS5A13FE9000	
			5.25-inch 2HD	μS5A10FE9000	
	IBM PC/AT or	PC DOS	3.5-inch 2HC	μS7B13FE9200	
	compatibles	+ Windows	5.25-inch 2HC	μS7B10FE9200	
Translator (FT78K3) ^{Note}		, ,	e data, obtained using thrce program for RA78K3.	,	
	Host machine			- Part number	
		OS	Distribution media		
	PC-9800 series	MS-DOS	3.5-inch 2HD	μS5A13FT78K3	
			5.25-inch 2HD	μS5A10FT78K3	
	IBM PC/AT or compatibles	PC DOS	3.5-inch 2HC	μS7B13FT78K3	
			5.25-inch 2HC	μS7B10FT78K3	
Fuzzy inference module (FI78K/III) ^{Note}	This program pe Translator.	This program performs fuzzy inference by linking the fuzzy knowledge data converted by Translator.			
	Host machine			Part number	
		OS	Distribution media		
	PC-9800 series	MS-DOS PC DOS	3.5-inch 2HD	μS5A13FI78K3	
			5.25-inch 2HD	μS5A10FI78K3	
	IBM PC/AT or		3.5-inch 2HC	μS7B13FI78K3	
	compatibles		5.25-inch 2HC	μS7B10FI78K3	
Fuzzy inference debugger (FD78K/III)		This software supports the evaluation and adjustment of fuzzy knowledge data at the hardware level, by using an in-circuit emulator.			
	Hoot machine				
	Host machine	00	Distribution modelin	- Part number	
		OS	Distribution media		
	PC-9800 series	MS-DOS	3.5-inch 2HD	μS5A13FD78K3	
				μS5A13FD78K3 μS5A10FD78K3	
			3.5-inch 2HD		

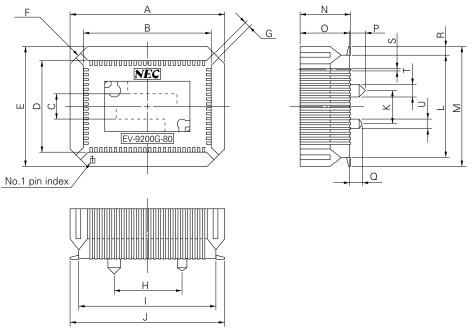
Note Under development



APPENDIX B DIMENSIONS OF THE CONVERSION SOCKET AND RECOMMENDED PATTERN ON BOARDS

Fig. B-1 Dimensions of the Conversion Socket (EV-9200G-80)(Reference)

Based on EV-9200G-80 (1) Package drawing (in mm)



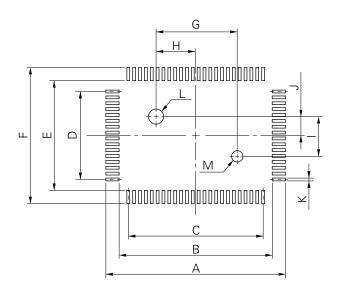
EV-9200G-80-G0

ITEM	MILLIMETERS	INCHES
А	25.0	0.984
В	20.30	0.799
С	4.0	0.157
D	14.45	0.569
E	19.0	0.748
F	4-C 2.8	4-C 0.11
G	0.8	0.031
Н	11.0	0.433
I	22.0	0.866
J	24.7	0.972
K	5.0	0.197
L	16.2	0.638
М	18.9	0.744
0	8.0	0.315
N	7.8	0.307
Р	2.5	0.098
Q	2.0	0.079
R	1.35	0.053
S	0.35±0.1	0.014 ^{+0.004} _{-0.005}
Т	φ2.3	φ0.091
U	φ1.5	φ0.059



Fig. B-2 Recommended Pattern on Boards for the Conversion Socket (EV-9200G-80)(Reference)

Based on EV-9200G-80 (2) Pad drawing (in mm)



EV-9200G-80-P0

ITEM	MILLIMETERS	INCHES
А	25.7	1.012
В	21.0	0.827
С	0.8±0.02 × 23=18.4±0.05	$0.031^{+0.002}_{-0.001} \times 0.906 = 0.724^{+0.003}_{-0.002}$
D	0.8±0.02 × 15=12.0±0.05	$0.031^{+0.002}_{-0.001} \times 0.591 = 0.472^{+0.003}_{-0.002}$
Е	15.2	0.598
F	19.9	0.783
G	11.00±0.08	0.433 ^{+0.004} _{-0.003}
Н	5.50±0.03	0.217 ^{+0.001} _{-0.002}
- 1	5.00±0.08	0.197 ^{+0.003} _{-0.004}
J	2.50±0.03	0.098+0.002
K	0.5±0.02	0.02 ^{+0.001} _{-0.002}
L	\$\phi_2.36\pmu_0.03\$	φ0.093 ^{+0.001} _{-0.002}
М	Ø1.57±0.03	φ0.062 ^{+0.001} _{-0.002}

Caution

Dimensions of mount pad for EV-9200 and that for target device (QFP) may be different in some parts. For the recommended mount pad dimensions for QFP, refer to "SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL" (IEI-1207).



Cautions on CMOS Devices

Countermeasures against static electricity for all MOSs

Caution When handling MOS devices, take care so that they are not electrostatically charged.

Strong static electricity may cause dielectric breakdown in gates. When transporting or storing MOS devices, use conductive trays, magazine cases, shock absorbers, or metal cases that NEC uses for packaging and shipping. Be sure to ground MOS devices during assembling. Do not allow MOS devices to stand on plastic plates or do not touch pins.

Also handle boards on which MOS devices are mounted in the same way.

CMOS-specific handling of unused input pins

Caution Hold CMOS devices at a fixed input level.

Unlike bipolar or NMOS devices, if a CMOS device is operated with no input, an intermediate-level input may be caused by noise. This allows current to flow in the CMOS device, resulting in a malfunction. Use a pull-up or pull-down resistor to hold a fixed input level. Since unused pins may function as output pins at unexpected times, each unused pin should be separately connected to the VDD or GND pin through a resistor.

If handling of unused pins is documented, follow the instructions in the document.

Statuses of all MOS devices at initialization

Caution The initial status of a MOS device is unpredictable when power is turned on.

Since characteristics of a MOS device are determined by the amount of ions implanted in molecules, the initial status cannot be determined in the manufacture process. NEC has no responsibility for the output statuses of pins, input and output settings, and the contents of registers at power on. However, NEC assures operation after reset and items for mode setting if they are defined.

When you turn on a device having a reset function, be sure to reset the device first.

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ITRON stands for Industrial TRON.

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Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

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